RXX00 SERIES

HIGH VOLTAGE SILICON RECTIFIER

产品规格确认书

R1200 THRU R2000

HIGH VOLTAGE SILICON RECTIFIER

康 比 電 子
HORNBY ELECTRONIC

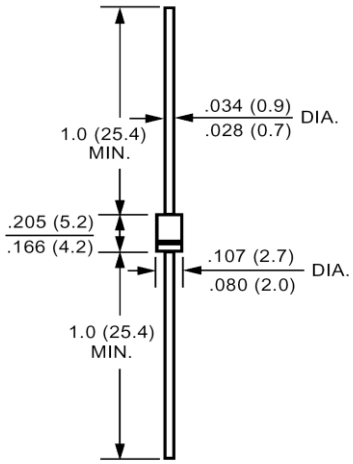
REVERSE VOLTAGE: **1200 to 2000 VOLTS**

FORWARD CURRENT: **0.2 to 0.5 AMPERE**

FEATURES

· Low cost
· Low leakage
· Low forward voltage drop
· High current capability

DO-41



Dimensions in inches and (millimeters)

MECHANICAL DATA

Case: Molded plastic, DO-41
Terminals: Axial leads, solderable per MIL-STD-202, method 208 guaranteed
Polarity: Band denotes cathode
Mounting position: Any
Weight: 0.013ounce, 0.3gram

Maximum Ratings and Electrical Characteristics

Ratings at 25℃ ambient temperature unless otherwise specified.
Single phase, half wave, 60H_Z, resistive or inductive load.
For capacitive load, derate current by 20%.

	Symbols	*R1200*	*R1500*	*R1800*	*R2000*	Units
Maximum Recurrent Peak Reverse Voltage	V_{RRM}	1200	1500	1800	2000	**Volts**
Maximum RMS Voltage	V_{RMS}	840	1050	1260	1400	**Volts**
Maximum DC Blocking Voltage	V_{DC}	1200	1500	1800	2000	**Volts**
Maximum Average Forward Rectified Current .375"(9.5mm) Lead Length at T_A=55℃	$I_{(AV)}$	0.5			0.2	**Amp**
Peak Forward Surge Current, 8.3ms single half-sine-wave superimposed on rated load (JEDEC method)	I_{FSM}	30				**Amp**
Maximum Forward Voltage at 0.5/0.2A	V_F	2.0			3.0	**Volts**
Maximum Reverse Current at T_A=25℃	I_R	5.0				**uAmp**
at Rated DC Blocking Voltage T_A=100℃		50				
Maximum Full Load Reverse Current Average, Full Cycle .375", (9.5mm) lead length at T_L = 75℃		30				**uAmp**
Typical Junction Capacitance (Note 1)	C_J	30				**pF**
Operating and Storage Temperature Range	T_J, Tstg	-55 to +150				**℃**

NOTES:

1- Measured at 1 MH_Z and applied reverse voltage of 4.0 VDC.

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RATINGS AND CHARACTERISTIC CURVES

FIG. 1 - TYPICAL FORWARD CURRENT DERATING CURVE

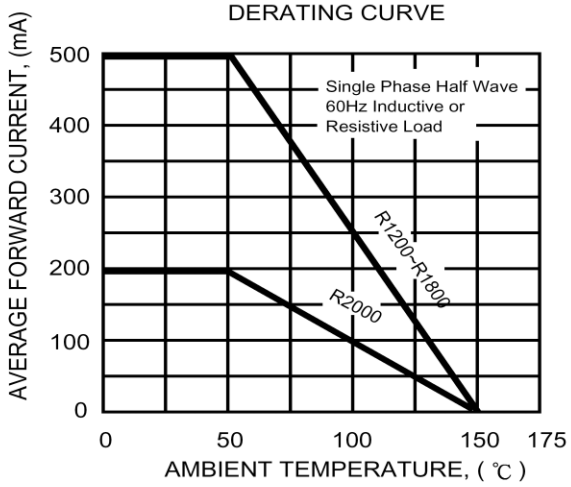

FIG. 2 - MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

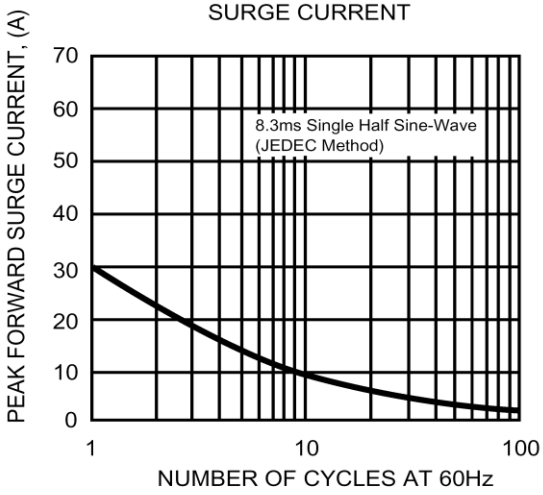

FIG. 3 - TYPICAL REVERSE CHARACTERISTICS